HITACHI

ADE-208-016B(Z)

HRW0503A
Silicon Schottky Barrier Diode for Rectifying

HITACHI

Rev. 2
Sep. 1994

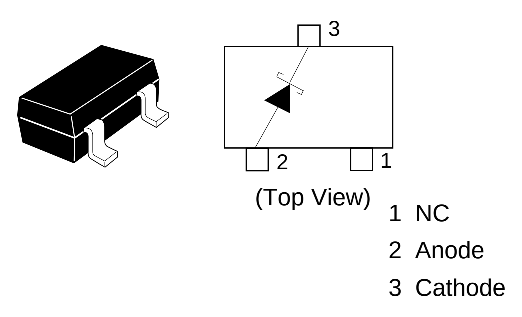
Features

- Low forward voltage drop and suitable for high effifiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRW0503A	S 6	MPAK

Pin Arrangement



1 NC
2 Anode
3 Cathode

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	I_o *	500	mA
Non-Repetitive peak forward surge current	I_{FSM}**	5	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

* Square wave, Duty (1/2)
** 10msec sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	50	µA	V_R = 30 V
Forward voltage	V_F	—	—	0.55	V	I_F = 500 mA
Capacitance	C	—	65	—	pF	V_R= 0 V, f = 1 MHz

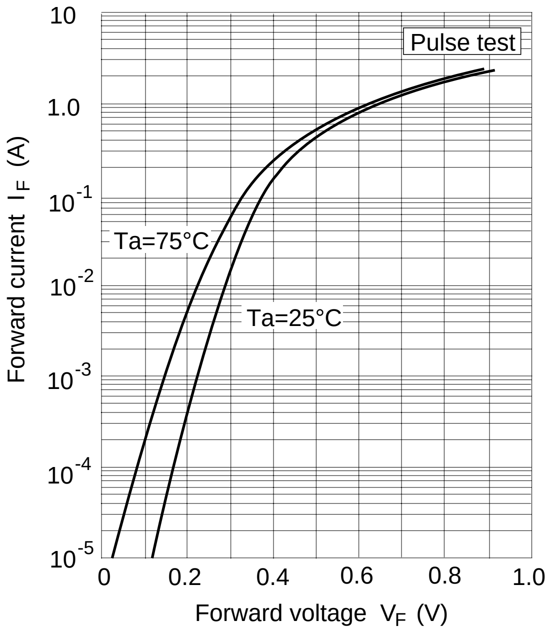


Fig.1 Forward current Vs. Forward voltage

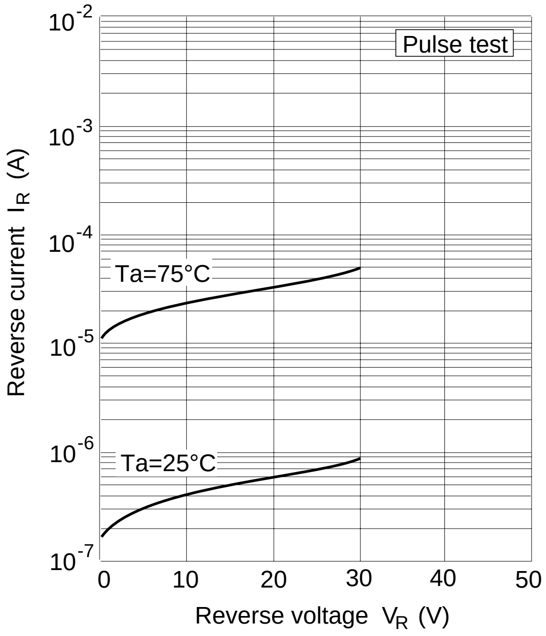


Fig.2 Reverse current Vs. Reverse voltage

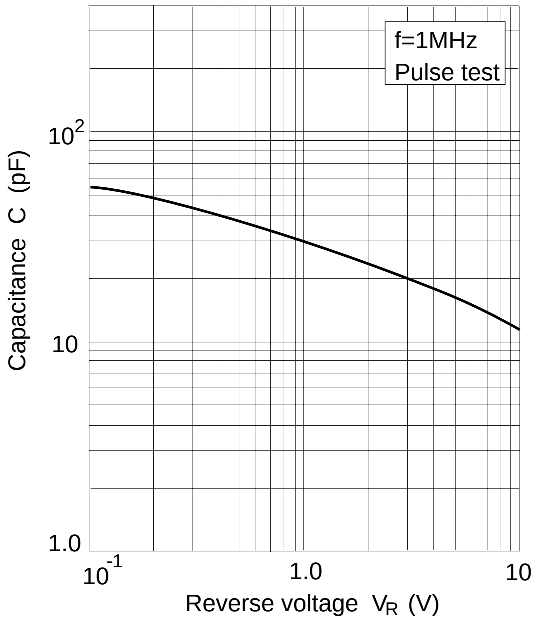
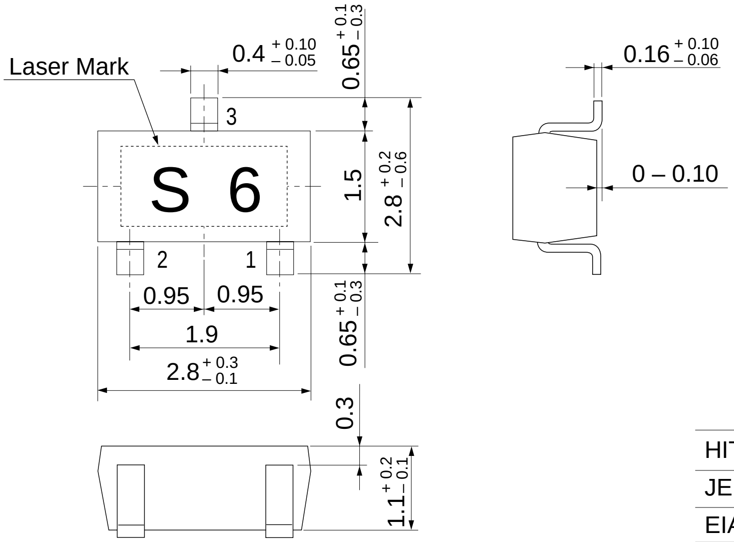


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1	NC
2	Anode
3	Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011